

P-Channel 30-V (D-S) MOSFET

| PRODUCT SUMMARY | | |
|-----------------|-----------------------------|-----------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) |
| - 30 | 0.035 at $V_{GS} = - 10$ V | - 6.2 |
| | 0.053 at $V_{GS} = - 4.5$ V | - 5.0 |

FEATURES

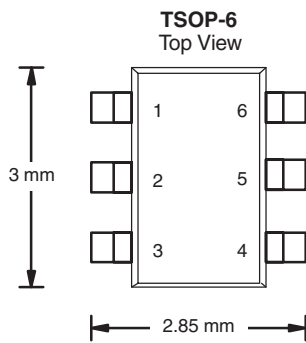
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Load Switch



P-Channel MOSFET

Ordering Information: Si3483DV-T1-E3 (Lead (Pb)-free)
Si3483DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | | | |
|--|----------------|---------------|--------------|-------|---|
| Parameter | Symbol | 5 s | Steady State | Unit | |
| Drain-Source Voltage | V_{DS} | - 30 | | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | | |
| Continuous Drain Current ($T_J = 150$ °C) ^a | I_D | $T_A = 25$ °C | - 6.2 | - 4.7 | A |
| | | $T_A = 70$ °C | - 4.9 | - 3.7 | |
| Pulsed Drain Current | I_{DM} | - 25 | | | |
| Continuous Source Current (Diode Conduction) ^a | I_S | - 1.7 | - 0.95 | | |
| Maximum Power Dissipation ^a | P_D | $T_A = 25$ °C | 2.0 | 1.14 | W |
| | | $T_A = 70$ °C | 1.3 | 0.73 | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|------------|--------------|---------|------|------|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^a | R_{thJA} | $t \leq 5$ s | 45 | 62.5 | °C/W |
| | | Steady State | 90 | 110 | |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 25 | 30 | | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

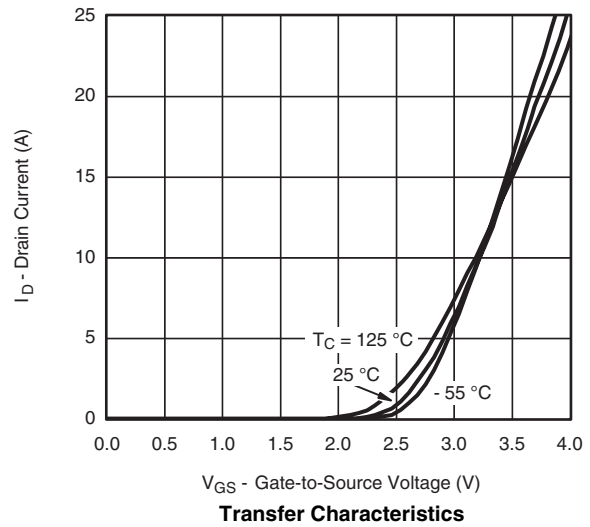
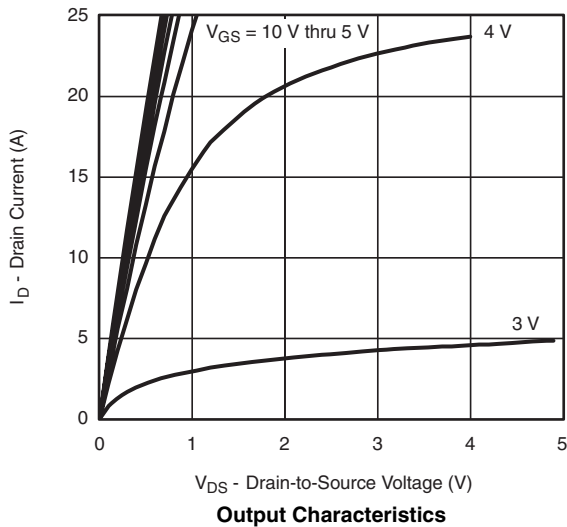
| SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|--------------|--|------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$ | -1.0 | | -3 | V |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$ | | | -1 | μA |
| | | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 85^\circ\text{C}$ | | | -5 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \leq -5 \text{ V}, V_{GS} = -10 \text{ V}$ | -25 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -10 \text{ V}, I_D = -6.2 \text{ A}$ | | 0.028 | 0.035 | Ω |
| | | $V_{GS} = -4.5 \text{ V}, I_D = -5.0 \text{ A}$ | | 0.042 | 0.053 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -15 \text{ V}, I_D = -6.2 \text{ A}$ | | 14 | | S |
| Diode Forward Voltage ^a | V_{SD} | $I_S = -1.7 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.8 | -1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -6.2 \text{ A}$ | | 23 | 35 | nC |
| Gate-Source Charge | Q_{gs} | | | 3.6 | | |
| Gate-Drain Charge | Q_{gd} | | | 6 | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -15 \text{ V}, R_L = 15 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 6 \Omega$ | | 10 | 15 | ns |
| Rise Time | t_r | | | 10 | 15 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 71 | 110 | |
| Fall Time | t_f | | | 45 | 70 | |
| Source-Drain Reverse Recovery Time | t_{rr} | $I_F = -1.7 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}$ | | 45 | 70 | |

Notes:

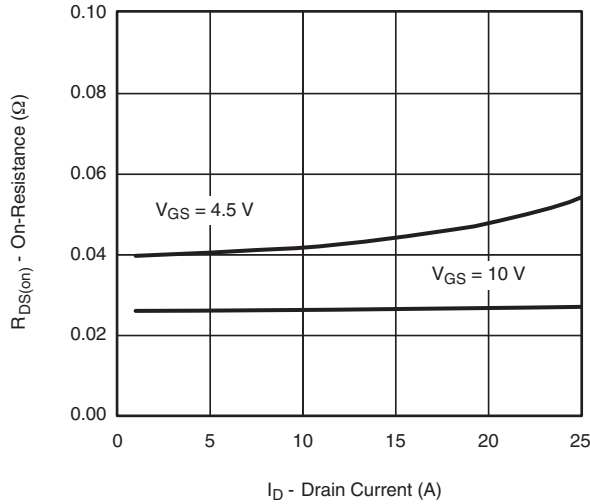
- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

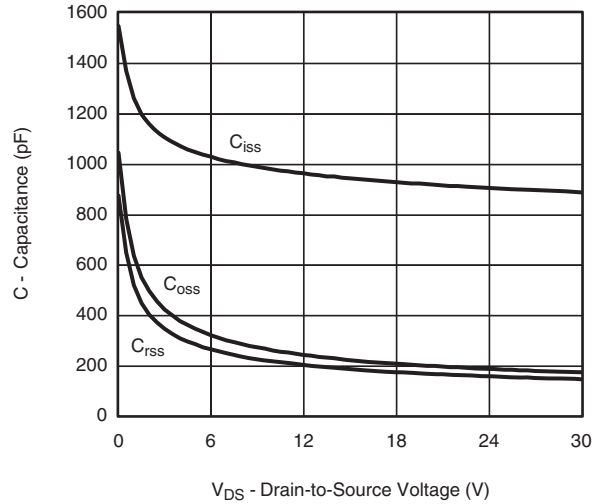
TYPICAL CHARACTERISTICS 25°C , unless otherwise noted



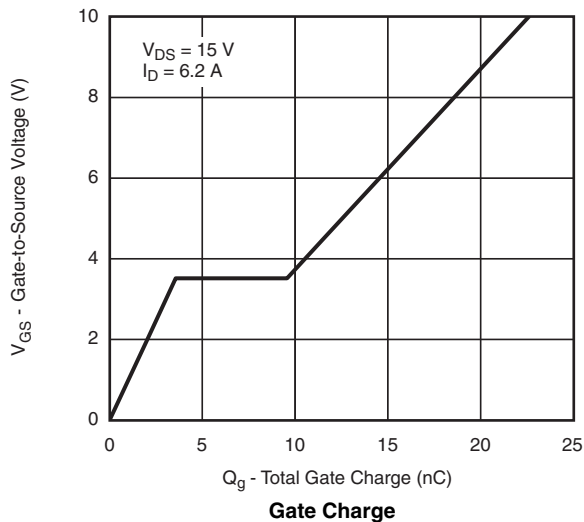
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



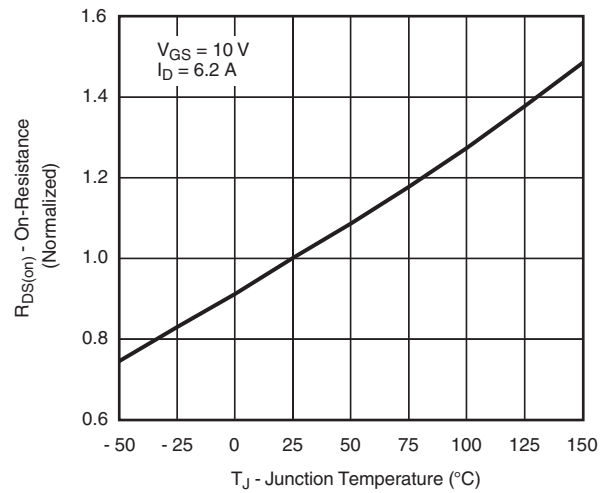
I_D - Drain Current (A)
On-Resistance vs. Drain Current



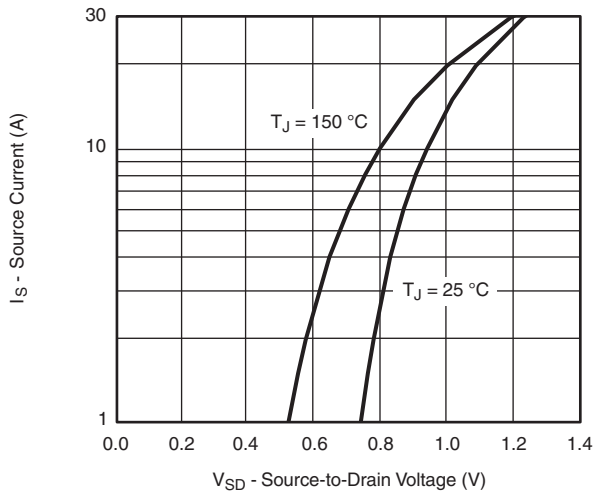
V_{DS} - Drain-to-Source Voltage (V)
Capacitance



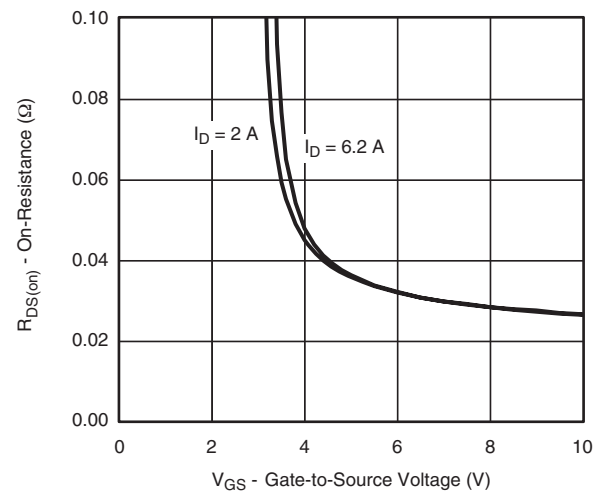
Q_g - Total Gate Charge (nC)
Gate Charge



T_J - Junction Temperature ($^{\circ}\text{C}$)
On-Resistance vs. Junction Temperature

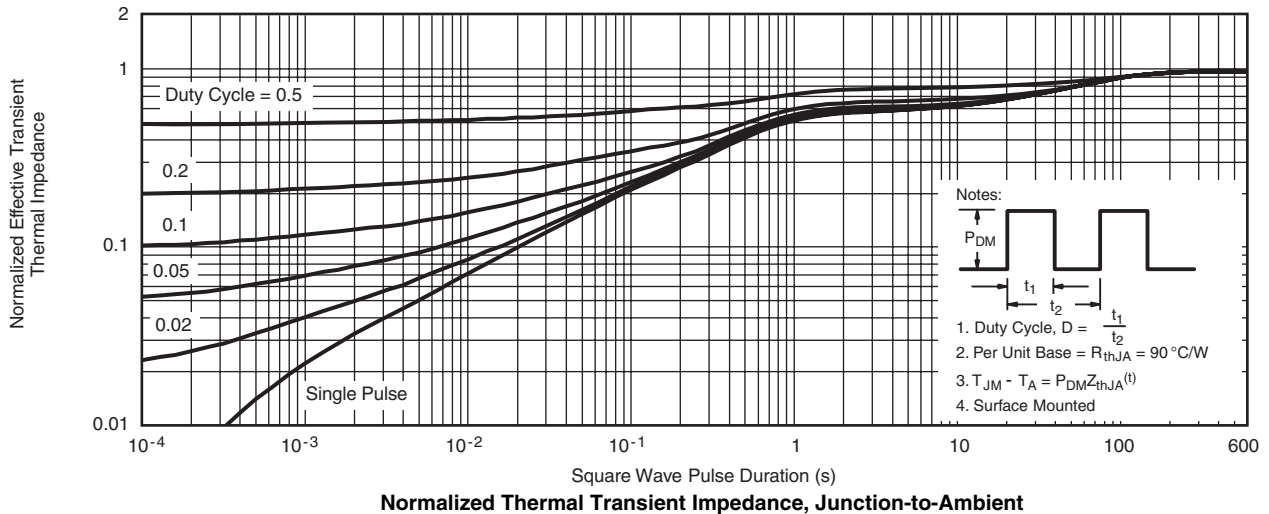
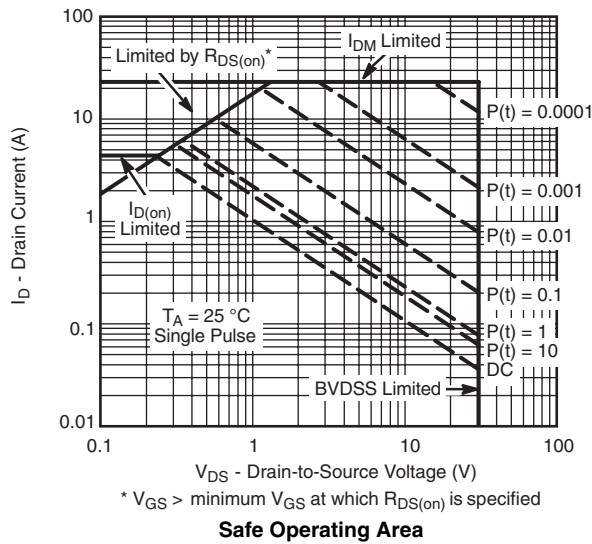
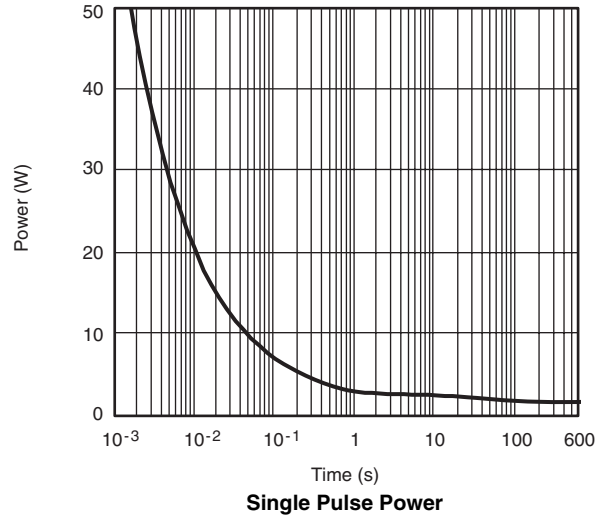
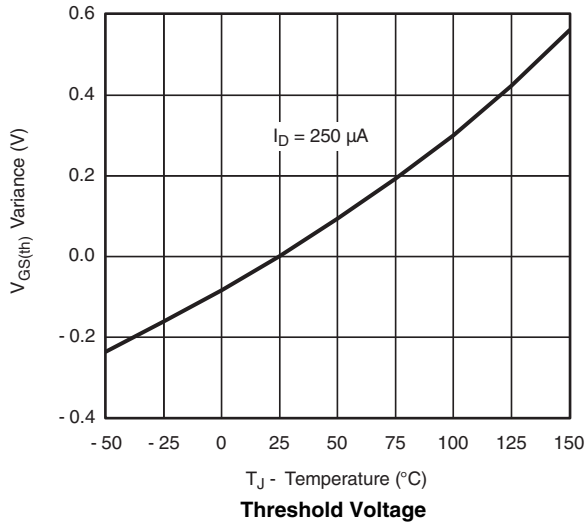


V_{SD} - Source-to-Drain Voltage (V)
Source-Drain Diode Forward Voltage

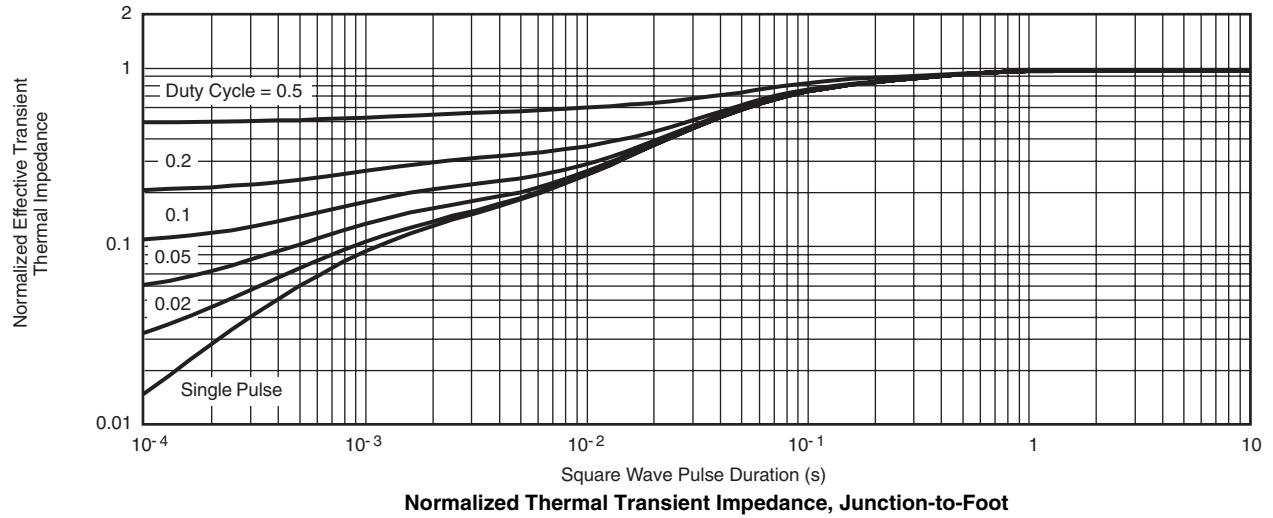


V_{GS} - Gate-to-Source Voltage (V)
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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